The investigation of the high frequency hopping conductivity in two- and three-dim ensional electron gas by an acoustic method.

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Abstract

H igh-frequency (HF) conductivity (hf) measured by an acoustical method has been studied in G aA s/A IG aA s heterostructures in a linear and nonlinear regime on acoustic power. It has been shown that in the quantum H all regime at magnetic elds corresponding to the middle of the H all plateaus the HF conductivity is determined by the sum of the conductivity of 2-dimensional electrons in the high-mobility channel and the hopping conductivity of the electrons in the doped thick A IG aA s layer. The dependence of these conductivities on a temperature is analyzed. The width of the Landau level broadened by the impurity random potential is determined.

PACS num bers: 72.50, 73.40.

Typeset using REVT_EX

I. IN TRODUCTION

If one places a sem iconducting heterostructure over a piezoelectric platelet along which acoustic surface wave (SAW) is being propagated, the SAW undergoes additional attenuation associated with the interaction of the electrons of heterostructure with the electric eld of SAW. This is the basis of the acoustic method pioneered by W ixforth [1] for the investigation of G aA s/A G aA s heterostructures. In contrast to [1] in the present work it has been found that in a G aA s/A G aA s heterostructure ($= 128 \ 10^5 \text{ cm} = \text{V s}$, $n = 6.7 \ 10^{11} \text{ cm}^2$) in the quantum H all regime the conductivities hf measurements: $_{dc} = 0$, whereas hf has a nite value depending on a temperature, magnetic eld and SAW intensity. And this is the main objective of the present work to elucidate the nature of this HF conductivity.

The theoretical absorption coe cient can be presented in the following way [2]:

$$= 8.68 \frac{K^{2}}{2} kA \frac{(4 _{xx} = _{s}v)c(k)}{1 + [(4 _{xx} = _{s}v)c(k)]^{2}}; A = 8b(k)(_{1} + _{0})^{2}_{0} exp(2ka);$$
(1)

where K² is the electrom echanical coupling coe cient of piezoelectric substrate, k and v are the SAW wavevector and the velocity respectively, a is the vacuum gap width between the lithium niobate platelet and the sample, $_{xx}$ is the dissipative HF conductivity of 2D EG, 1, 0 and $_{s}$ are the dielectric constants of lithium niobate, vacuum and sem iconductor respectively; b and c are some complex functions of a, k, 1, 0 and $_{s}$. When (4 $_{xx}=_{s}v)c(k)=1$,

achieves the maximum $_{\rm m}$. In the case when $_{\rm xx}=v<<1$ (quantum Hallregine) / $_{\rm xx}$. Thus, the SAW electronic attenuation may be taken as a measure of the heterostructure conductivity.

The measurements were carried out in a temperature range 1.5-4.2K, and magnetic elds B up to 7T, with an acoustic frequency in the range of 30-150 MHz. Two kinds of measurements were performed: for the rst kind the acoustic power maintained low enough to provide the linearity of results, for the second kind a nonlinear behavior on acoustic power P level was studied intensively at 1.5K.

II. EXPER IM ENTAL RESULTS AND DISCUSSION

Fig.1 illustrates the experim ental dependences of on B.As long as the SAW attenuation factor is determined by the sample conductivity, quantizing of the electron spectrum in a magnetic eld, leading to the SdH oscillations should result in similar peculiarities of the curves of Fig 1. In the present work the experimental data for the magnetic elds corresponding to the quantum Hall regime will be analyzed.

Fig2 presents the = m (T) dependences (f= 30 M Hz) at magnetic elds 4.8, 3.6, and 2.9T corresponding to the attenuation m inim a (or the m iddle of the Hall plateau), which are deduced from the curves of Fig.1, measured at di erent T and f. As one can see from the gure, as T grows, in a certain temperature range does not depend on a temperature, but at higher temperature begins to grow exponentially, the stronger B, the higher T at which the grow th starts.

Such a dependence could not be explained, if one supposes that (T) is determ ined solely by the 2-dimensional electrons. Indeed, in the quantum Hall regime when the Ferm i level is

in the middle between two Landau levels, in the temperature range 1.5-4.2 K the temperature dependence of the 2-dimensional conductivity $_2$ (and corresponding attenuation $_2$) is governed by the activation of electrons from the bound states at the Ferm i level to the upper Landau band, i.e. $_2 / _2 / \exp(E_g = kT)$.

The dependence of on tem perature could be explained, if one supposes that at these levels of B the attenuation adds up both from the SAW attenuation $_2$ by the 2-dim ensional electrons, and $_h$, due to the electrons, localized on the impurities in the quasi-3-dim ensional A IG aA s layer, which supplies carriers to the 2-dim ensional channel.

A coording to β {5] in a transverse magnetic eld $_{\rm h}$ / $_{\rm h}$ / !B ² and does not depend on a tem perature. Thus the independence of on a tem perature at low T could be interpreted as a dom inance of the conductivity of the quasi-3-dimensional layer. As T rises the 2dimensional conductivity becomes prevailing. Based on the above arguments, $_2$ has been determined as a difference between the experimentally obtained values of and $_{\rm h}$. $_{\rm h}$ is equal to the in the temperature range where is temperature-independent at the magnetic elds 4.8 and 3.6T ($_2 << _{\rm h}$). At B = 2.9T, when there is no temperature attening , $_{\rm h}$ was obtained, using the assumption that $_{\rm h}$ / 1=B², [5]. From the plotted dependence lg $_2$ (1=T) the activation energy E $_{\rm g}$ has been found at B = 4.8, 3.6, 2.9 T. Fig.3 shows the E $_{\rm g}$ dependence on B. The activation energy obtained from the curves at different magnetic elds appeared to be less than the corresponding energy h! c=2. This may be due to the Landau level broadening A caused by the random uctuation potential.

Supposing E $_{g}$ = h! $_{c}$ =2 A=2, where h is the Plank constant, ! $_{c}$ = eB =m c is the cyclotron frequency, from the ordinate cut-o point of the E $_{g}$ (B) = 0 curve for B = 2.1T one could obtain A, which appeared to be 3.4 m eV. The slope of the E $_{g}$ (B) line in g.3 appeared to be 0.72 1/B, which by 10% di ers from the value e-m c= 0.8 1/B, if m = 0.07m $_{0}$ for G aA s (m $_{0}$ - free electron m ass).

The dependence of = m on P at the same magnetic eld is shown in g.4. It can be seen from the gure, that increases with the increase of P. K eeping in m ind that at given m agnetic elds ₂ is determined by the electron activation to the upper Landau band from the Fermilevel, one could suppose that Frenkel-Poole ectie the activation energy decrease in electric eld E of a SAW [6] is operative in this case.

$$_{2} / _{2} / n (T; E) = n_{0} \exp (2e^{3-2}E^{1-2} s^{1-2} = kT);$$
 (2)

where n_0 -carrier density in the upper Landau level at a linear approach at 1.5K. Ln ₂ plotted against E ¹⁼², where ₂ = _h, and E is the electric eld of SAW [7], which can be presented by a straight line, con rm s our model.

III.CONCLUSION

High-frequency conductivity $_{\rm hf}$ of a G aA s/A is a sheterostructure with a moderate mobility has been studied in the quantum Hall regime ($_{\rm dc}$ = 0) by an acoustic contactless method. It has been shown that up to T = 2K $_{\rm hf}$ is determined by the hopping conductivity in thick, quasi three-dimensional layers of A is a swell described by a Pollak-G eballe model [3]. The two-dimensional HF conductivity in the quantum Hall regime is governed by the electron activation into the upper Landau band. The small value of this conductivity allows one to suppose it also to be of a hopping nature, but this point needs further arguments to be proved.

The work was supported by the RFFIN 95-02-04066-a and MINNAUKIN 97-1043 grants.

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FIGURES

FIG.1. The experimental dependence of absorption coe-cient % T=4.2K .

FIG.2. The dependences of $=_m$ (f = 30M H z) on T at magnetic elds: 1-4.8T, 2-3.6T, 3-2.9T.

FIG.3. The dependences of on magnetic eld for two frequencies: 1-30M Hz, 2-150M Hz.

FIG.4. The dependences of = m on the RF-generator output power in m agnetic elds: 1-4.8T, 2-3.6T, 3-2.9T.







